

www.ti.com

## HIGH-SPEED DIFFERENTIAL RECEIVERS

#### **FEATURES**

- 400-Mbps Signaling Rate<sup>(1)</sup> and 200-Mxfr/s Data Transfer Rate
- Operates With a Single 3.3-V Supply
- -4 V to 5 V Common-Mode Input Voltage Range
- Differential Input Thresholds <±50 mV With 50 mV of Hysteresis Over Entire Common-Mode Input Voltage Range
- Integrated 110- $\Omega$  Line Termination Resistors On LVDT Products
- TSSOP Packaging (33 Only)
- Complies With TIA/EIA-644 (LVDS)
- Active Failsafe Assures a High-Level Output With No Input
- Bus-Pin ESD Protection Exceeds 15 kV HBM
- Input Remains High-Impedance on Power Down
- TTL Inputs Are 5 V Tolerant
- Pin-Compatible With the AM26LS32, SN65LVDS32B, µA9637, SN65LVDS9637B
- (1) The signalling rate of a line, is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

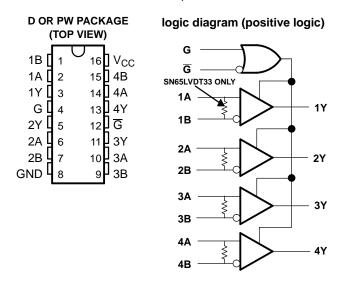
#### **DESCRIPTION**

This family of four LVDS data line receivers offers the widest common-mode input voltage range in the industry. These receivers provide an input voltage range specification compatible with a 5-V PECL signal as well as an overall increased ground-noise tolerance. They are in industry standard footprints with integrated termination as an option.

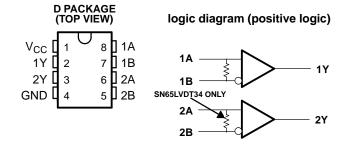
Precise control of the differential input voltage thresholds allows for inclusion of 50 mV of input voltage hysteresis to improve noise rejection on slowly changing input signals. The input thresholds are still no more than ±50 mV over the full input common-mode voltage range.

The high-speed switching of LVDS signals usually necessitates the use of a line impedance matching resistor at the receiving-end of the cable or transmission media. The SN65LVDT series of receivers eliminates this external resistor by integrating it with the receiver. The nonterminated SN65LVDS series is also available for multidrop or other termination circuits.

#### SN65LVDS33D, SN65LVDT33D SN65LVDS33PW, SN65LVDT33PW



#### SN65LVDS34D, SN65LVDT34D





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **AVALIABLE OPTIONS**(1)

PART NUMBER <sup>(2)</sup>	NUMBER OF RECEIVERS	TERMINATION RESISTOR	SYMBOLIZATION
SN65LVDS33D	4	No	LVDS33
SN65LVDS33PW	4	No	LVDS33
SN65LVDTS33D	4	Yes	LVDT33
SN65LVDT33PW	4	Yes	LVDT33
SN65LVDS34D	2	No	LVDS34
SN65LVDT34D	2	Yes	LVDS34

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI
website at www.ti.com.

## **DESCRIPTION (CONTINUED)**

The receivers can withstand ±15 kV human-body model (HBM) and ±600 V machine model (MM) electrostatic discharges to the receiver input pins with respect to ground without damage. This provides reliability in cabled and other connections where potentially damaging noise is always a threat.

The receivers also include a (patent pending) failsafe circuit that will provide a high-level output within 600 ns after loss of the input signal. The most common causes of signal loss are disconnected cables, shorted lines, or powered-down transmitters. The failsafe circuit prevents noise from being received as valid data under these fault conditions. This feature may also be used for Wired-Or bus signaling. See *The Active Failsafe Feature of the SN65LVDS32B* application note.

The intended application and signaling technique of these devices is point-to-point baseband data transmission over controlled impedance media of approximately 100  $\Omega$ . The transmission media may be printed-circuit board traces, backplanes, or cables. The ultimate rate and distance of data transfer is dependent upon the attenuation characteristics of the media and the noise coupling to the environment.

The SN65LVDS33, SN65LVDT33, SN65LVDS34 and SN65LVDT34 are characterized for operation from -40°C to 85°C.

#### Function Tables<sup>(1)</sup>

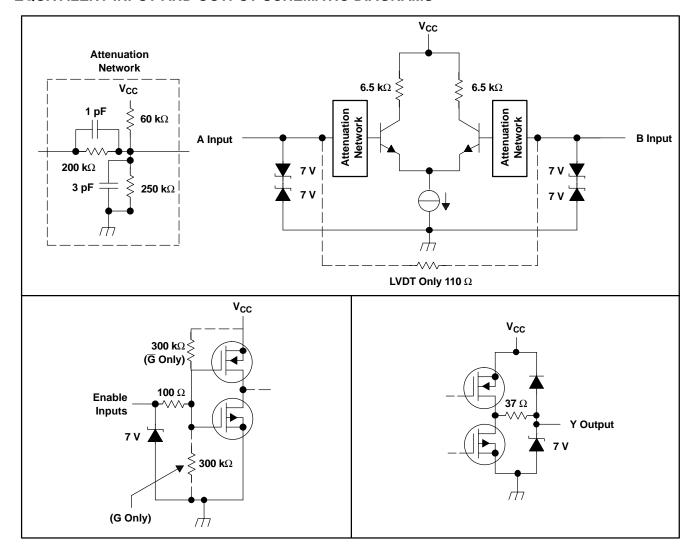
SN65LVDS33 and	SN65L	VDT33		SN65LVDS34 and SN65	LVDT34
DIFFERENTIAL INPUT	ENABLES C		OUTPUT	DIFFERENTIAL INPUT	OUTPUT
$V_{ID} = V_A - V_B$	G	G	Υ	$V_{ID} = V_A - V_B$	Υ
V <sub>ID</sub> ≥ -32 mV	Н	Х	Н	$V_{ID} \ge -32 \text{ mV}$	Н
VID ≥ -32 IIIV	Х	L	Н	$-100 \text{ mV} < V_{\text{ID}} \le -32 \text{ mV}$	?
-100 mV < V <sub>ID</sub> ≤ -32 mV	Н	Х	?	$V_{ID} \le -100 \text{ mV}$	L
-100 1110 < V <sub>ID</sub> ≤ -32 1110	Х	L	?	Open	Н
V <sub>ID</sub> ≤ −100 mV	Н	Х	L		
V <sub>ID</sub> ≤ −100 111V	Х	L	L		
X	L	Н	Z		
Open	Н	Х	Н		
Ореп	Х	L	Н		

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off), ? = indeterminate

<sup>(2)</sup> Add the suffix R for taped and reeled carrier.



### **EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS**





#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)(1)

		UNIT	
Supply voltage range, V <sub>CC</sub>	<sub>2</sub> (2)	-0.5 V to 4 V -1 V to 6 V -5 V to 6 V 1 V Class 3, A: 15 kV, B: 500 V ±500 V	
	Enables or Y	-1 V to 6 V	
Voltage range	A or B	–5 V to 6 V	
	V <sub>A</sub> - V <sub>B</sub>   (LVDT)	1 V	
Electrostatic discharge	A, B, and GND <sup>(3)</sup>	Class 3, A: 15 kV, B: 500 V	
Charged-device mode	All pins <sup>(4)</sup>	±500 V	
Continuous power dissipa	tion	See Dissipation Rating Table	
Storage temperature rang	e	-65°C to 150°C	
Lead temperature 1,6 mm	(1/16 inch) from case for 10 seconds	260°C	

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
- (3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
- (4) Tested in accordance with JEDEC Standard 22, Test Method C101.

#### **DISSIPATION RATING TABLE**

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	OPERATING FACTOR <sup>(1)</sup> ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 85°C POWER RATING
D8	725 mW	5.8 mW/°C	377 mW
PW16	774 mW	6.2 mW/°C	402 mW
D16	950 mW	7.6 mW/°C	494 mW

<sup>(1)</sup> This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

#### RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		3	3.3	3.6	V
V <sub>IH</sub>	High-level input voltage	Enables	2		5	V
V <sub>IL</sub>	Low-level input voltage	Enables	0		8.0	V
1.1/	Magnitude of differential input voltage	LVDS	0.1		3	V
V <sub>ID</sub>	Magnitude of differential input voltage	LVDT			8.0	V
V <sub>I</sub> or V <sub>IC</sub>	Voltage at any bus terminal (separately o	r common-mode)	-4		5	V
T <sub>A</sub>	Operating free-air temperature		-40		85	°C



## **ELECTRICAL CHARACTERISTICS**

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT	
V <sub>IT1</sub>	Positive-going differential inp		V <sub>IB</sub> = -4 V or 5 V,			50	mV	
$V_{IT2}$	threshold	put voltage	See Figure 1 and Figure 2	-50				
V <sub>IT3</sub>	Differential input failsafe volt	input voltage  bitage threshold ysteresis,  SN65LVDx33 SN65LVDx34  SN65LVDS  SN65LVDT  SN65LVDS SN65LVDT  SN65LVDT  SN65LVDT  SN65LVDT	See Table 1 and Figure 5	-32		-100	mV	
V <sub>ID(HYS)</sub>	Differential input voltage hys V <sub>IT1</sub> - V <sub>IT2</sub>	teresis,			50		mV	
$V_{OH}$	High-level output voltage		$I_{OH} = -4 \text{ mA}$	2.4			V	
$V_{OL}$	Low-level output voltage		I <sub>OL</sub> = 4 mA			0.4	V	
		SN651 \/Dv33	G at V <sub>CC</sub> , No load, Steady-state		16	23		
I <sub>CC</sub> Supply current	Supply current	SINOSEVEXOS	G at GND		1.1	5	mA	
		SN65LVDx34	No load, Steady-state	8		12		
	Input current		V <sub>I</sub> = 0 V, Other input open					
		SNESI VDS	V <sub>I</sub> = 2.4 V, Other input open			±20	μA	
		SINOSEVES	$V_I = -4 \text{ V}$ , Other input open	±75			μΛ	
			V <sub>I</sub> = 5 V, Other input open			±40	0	
I <sub>I</sub>	(A or B inputs)		V <sub>I</sub> = 0 V, Other input open			±40		
		SN65LVDT	V <sub>I</sub> = 2.4 V, Other input open			±40	μA	
		ONOSEVET	$V_I = -4 V$ , Other input open			±150	μΛ	
			V <sub>I</sub> = 5 V, Other input open			±80		
I <sub>ID</sub>	Differential input current	SN65LVDS	$V_{ID} = 100 \text{ mV}, V_{IC} = -4 \text{ V or 5 V}$			±3	μΑ	
טוי	$(I_{IA} - I_{IB})$	SN65LVDT	$V_{ID} = 200 \text{ mV}, V_{IC} = -4 \text{ V or 5 V}$	1.55		2.22	mA	
		SN65LVDS	$V_A$ or $V_B = 0$ V or 2.4 V, $V_{CC} = 0$ V			±20		
l	Power-off input current	ONOSEVBO	$V_A$ or $V_B = -4$ or 5 V, $V_{CC} = 0$ V			±50	μA	
I <sub>I(OFF)</sub>	(A or B inputs)	SN65LVDT	$V_A$ or $V_B = 0$ V or 2.4 V, $V_{CC} = 0$ V			±30	μΛ	
		ONOSEVET	$V_A$ or $V_B = -4 \text{ V}$ or 5 V, $V_{CC} = 0 \text{ V}$			±100		
I <sub>IH</sub>	High-level input current (ena	bles)	V <sub>IH</sub> = 2 V			10	μΑ	
I <sub>IL</sub>	Low-level input current (enal	oles)	V <sub>IL</sub> = 0.8 V			10	μΑ	
l <sub>OZ</sub>	High-impedance output curre	ent		-10		10	μΑ	
C <sub>I</sub>	Input capacitance, A or B input	out to GND	$V_I = 0.4 \sin (4E6\pi t) + 0.5 V$		5		pF	

<sup>(1)</sup> All typical values are at 25°C and with a 3.3 V supply.



### SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
t <sub>PLH(1)</sub>	Propagation delay time, low-to-high-level output	Coo Figure 2	2.5	4	6	ns
t <sub>PHL(1)</sub>	Propagation delay time, high-to-low-level output	See Figure 3	2.5	4	6	ns
t <sub>d1</sub>	Delay time, failsafe deactivate time	C <sub>L</sub> = 10 pF, See Figure 3			9	ns
t <sub>d2</sub>	Delay time, failsafe activate time	and Figure 6	0.3		1.5	μs
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL(1)</sub> - t <sub>PLH(1)</sub>  )			200		ps
t <sub>sk(o)</sub>	Output skew <sup>(2)</sup>			150		ps
t <sub>sk(pp)</sub>	Part-to-part skew <sup>(3)</sup>	See Figure 3			1	ns
t <sub>r</sub>	Output signal rise time			0.8		ns
t <sub>f</sub>	Output signal fall time			0.8		ns
t <sub>PHZ</sub>	Propagation delay time, high-level-to-high-impedance output			5.5	9	ns
$t_{PLZ}$	Propagation delay time, low-level-to-high-impedance output	Soo Figure 4		4.4	9	ns
t <sub>PZH</sub>	Propagation delay time, high-impedance -to-high-level output	See Figure 4		3.8	9	ns
t <sub>PZL</sub>	Propagation delay time, high-impedance-to-low-level output			7	9	ns

- All typical values are at 25°C and with a 3.3-V supply.  $t_{sk(0)}$  is the magnitude of the time difference between the  $t_{PLH}$  or  $t_{PHL}$  of all receivers of a single device with all of their inputs driven together. (2)
- $t_{sk(pp)}$  is the magnitude of the time difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits. (3)

### PARAMETER MEASUREMENT INFORMATION

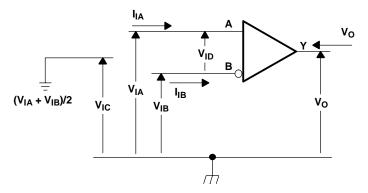
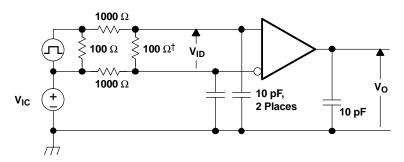


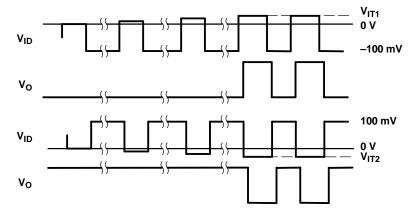
Figure 1. Voltage and Current Definitions



## PARAMETER MEASUREMENT INFORMATION (continued)



† Remove for testing LVDT device.

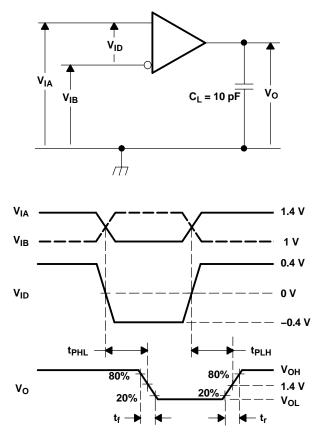


NOTE: Input signal of 3 Mpps, duration of 167 ns, and transition time of <1 ns.

Figure 2.  $V_{\text{IT1}}$  and  $V_{\text{IT2}}$  Input Voltage Threshold Test Circuit and Definitions



## PARAMETER MEASUREMENT INFORMATION (continued)

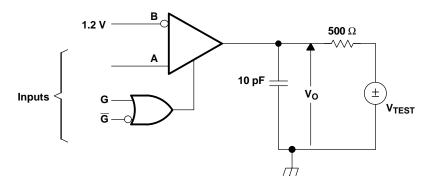


A. All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$  ns, pulse repetition rate (PRR) = 50 Mpps, pulsewidth = 10 ±0.2 ns.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 3. Timing Test Circuit and Waveforms



## PARAMETER MEASUREMENT INFORMATION (continued)



NOTE: All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \leq 1$  ns, pulse repetition rate (PRR) = 0.5 Mpps, pulsewidth = 500  $\pm 10$  ns .  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

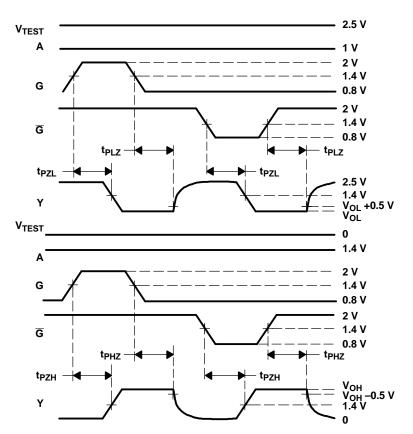


Figure 4. Enable/Disable Time Test Circuit and Waveforms



Table 1. Receiver Minimum and Maximum  $V_{\rm IT3}$  Input Threshold Test Voltages

APPLIED '	/OLTAGES <sup>(1)</sup>	RESULTANT INPUTS					
V <sub>IA</sub> (mV)	V <sub>IB</sub> (mV)	V <sub>ID</sub> (mV)	V <sub>IC</sub> (mV)	Output			
-4000	-3900	-100	-3950	L			
-4000	-3968	-32	-3984	Н			
4900	5000	-100	4950	L			
4968	5000	-32	4984	Н			

(1) These voltages are applied for a minimum of 1.5  $\mu$ s.

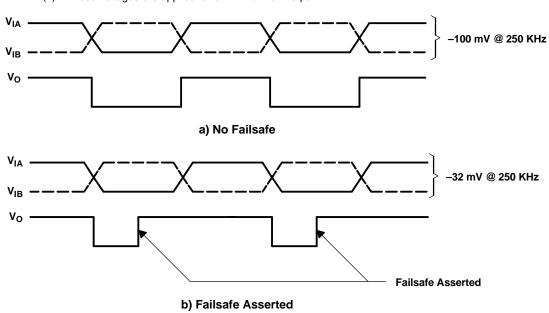


Figure 5. V<sub>IT3</sub> Failsafe Threshold Test

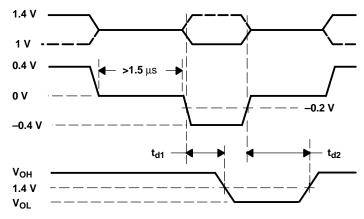


Figure 6. Waveforms for Failsafe Activate and Deactivate

HIGH-LEVEL OUTPUT VOLTAGE

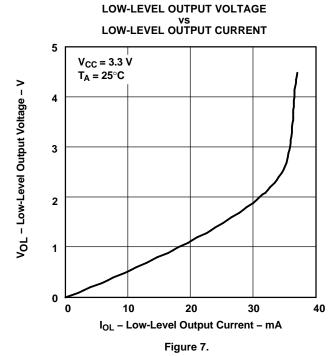
vs HIGH-LEVEL OUTPUT CURRENT

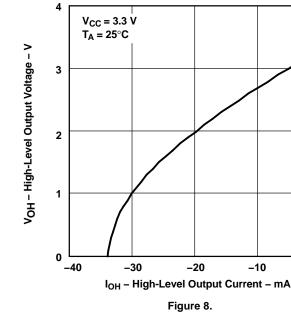
-20

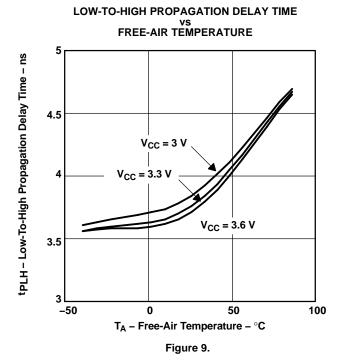
-10

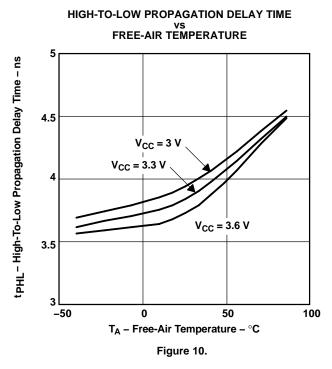


### **TYPICAL CHARACTERISTICS**



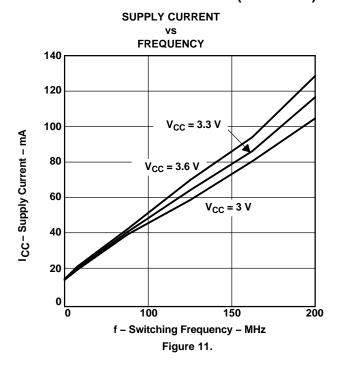




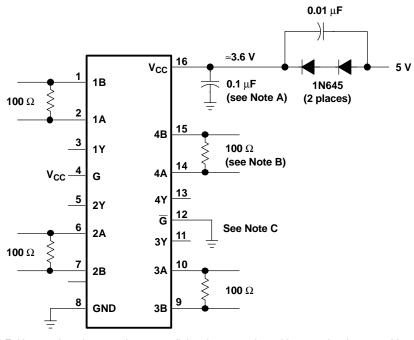




## **TYPICAL CHARACTERISTICS (continued)**



#### APPLICATION INFORMATION



- A. Place a  $0.1-\mu F$  Z5U ceramic, mica or polystyrene dielectric, 0805 size, chip capacitor between  $V_{CC}$  and the ground plane. The capacitor should be located as close as possible to the device terminals.
- B. The termination resistance value should match the nominal characteristic impedance of the transmission media with ±10%.
- C. Unused enable inputs should be tied to  $V_{\text{CC}}$  or GND as appropriate.

Figure 12. Operation With 5-V Supply



### **APPLICATION INFORMATION (continued)**

#### RELATED INFORMATION

IBIS modeling is available for this device. Contact the local TI sales office or the TI Web site at www.ti.com for more information.

For more application guidelines, see the following documents:

- Low-Voltage Differential Signalling Design Notes (SLLA014)
- Interface Circuits for TIA/EIA-644 (LVDS) (SLLA038)
- Reducing EMI With LVDS (SLLA030)
- Slew Rate Control of LVDS Circuits (SLLA034)
- Using an LVDS Receiver With RS-422 Data (SLLA031)
- Evaluating the LVDS EVM (SLLA033)

#### **ACTIVE FAILSAFE FEATURE**

A differential line receiver commonly has a failsafe circuit to prevent it from switching on input noise. Current LVDS failsafe solutions require either external components with subsequent reductions in signal quality or integrated solutions with limited application. This family of receivers has a new integrated failsafe that solves the limitations seen in present solutions. A detailed theory of operation is presented in application note *The Active Failsafe Feature of the SN65LVDS32B*, (SLLA082A).

The following figure shows one receiver channel with active failsafe. It consists of a main receiver that can respond to a high-speed input differential signal. Also connected to the input pair are two failsafe receivers that form a window comparator. The window comparator has a much slower response than the main receiver and it detects when the input differential falls below 80 mV. A 600-ns failsafe timer filters the window comparator outputs. When failsafe is asserted, the failsafe logic drives the main receiver output to logic high.

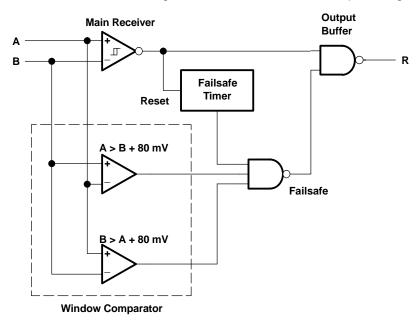


Figure 13. Receiver With Active Failsafe

#### ECL/PECL-TO-LVTTL CONVERSION WITH TI'S LVDS RECEIVER

The various versions of emitter-coupled logic (i.e., ECL, PECL and LVPECL) are often the physical layer of choice for system designers. Designers know of the established technology and that it is capable of high-speed data transmission. In the past, system requirements often forced the selection of ECL. Now technologies like



### **APPLICATION INFORMATION (continued)**

LVDS provide designers with another alternative. While the total exchange of ECL for LVDS may not be a design option, designers have been able to take advantage of LVDS by implementing a small resistor divider network at the input of the LVDS receiver. TI has taken the next step by introducing a wide common-mode LVDS receiver (no divider network required) which can be connected directly to an ECL driver with only the termination bias voltage required for ECL termination (V<sub>CC</sub>-2 V).

Figure 14 and Figure 15 show the use of an LV/PECL driver driving 5 meters of CAT-5 cable and being received by Tl's wide common-mode receiver and the resulting eye-pattern. The values for R3 are required in order to provide a resistor path to ground for the LV/PECL driver. With no resistor divider, R1 simply needs to match the characteristic load impedance of 50  $\Omega$ . The R2 resistor is a small value and is intended to minimize any possible common-mode current reflections.

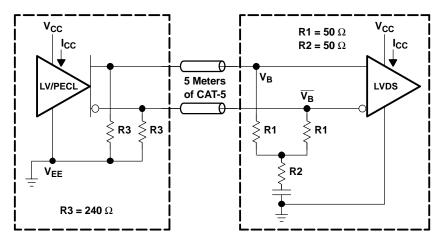


Figure 14. LVPECL or PECL to Remote Wide Common-Mode LVDS Receiver

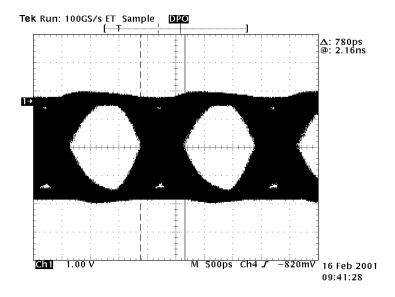


Figure 15. LV/PECL to Remote SN65LVDS33 at 500 Mbps Receiver Output (CH1)

#### **TEST CONDITIONS**

- V<sub>CC</sub> = 3.3 V
- T<sub>A</sub> = 25°C (ambient temperature)
- All four channels switching simultaneously with NRZ data. Scope is pulse-triggered simultaneously with NRZ data.



## **APPLICATION INFORMATION (continued)**

#### **EQUIPMENT**

- Tektronix PS25216 programmable power supply
- Tektronix HFS 9003 stimulus system
- Tektronix TDS 784D 4-channel digital phosphor oscilloscope DPO

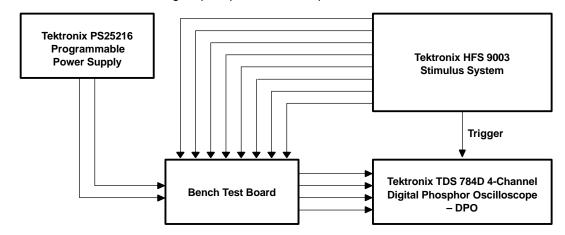


Figure 16. Equipment Setup

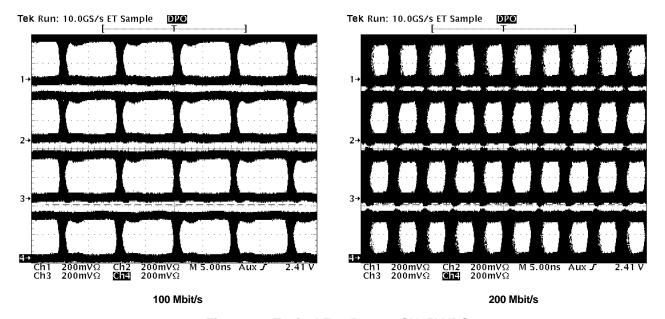


Figure 17. Typical Eye Pattern SN65LVDS33



## **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65LVDS33D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS33DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS33DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS33DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS33PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS33PWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS33PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS33PWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS34D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS34DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS34DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS34DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33PWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT33PWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT34D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT34DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT34DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT34DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

 $<sup>^{(1)}</sup>$  The marketing status values are defined as follows:



### PACKAGE OPTION ADDENDUM

18-Sep-2008

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN65LVDS33:

Enhanced Product: SN65LVDS33-EP

NOTE: Qualified Version Definitions:

Enhanced Product - Supports Defense, Aerospace and Medical Applications



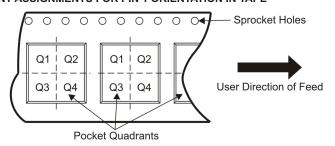
### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

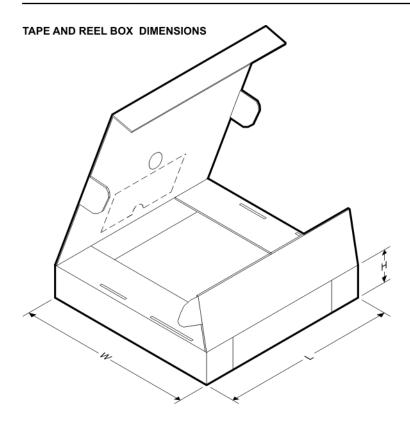
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDS33DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65LVDS33PWR	TSSOP	PW	16	2000	330.0	12.4	6.67	5.4	1.6	8.0	12.0	Q1
SN65LVDS34DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LVDS34DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LVDT33DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65LVDT33PWR	TSSOP	PW	16	2000	330.0	12.4	6.67	5.4	1.6	8.0	12.0	Q1
SN65LVDT34DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1





\*All dimensions are nominal

	1						
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS33DR	SOIC	D	16	2500	333.2	345.9	28.6
SN65LVDS33PWR	TSSOP	PW	16	2000	346.0	346.0	29.0
SN65LVDS34DR	SOIC	D	8	2500	340.5	338.1	20.6
SN65LVDS34DR	SOIC	D	8	2500	346.0	346.0	29.0
SN65LVDT33DR	SOIC	D	16	2500	346.0	346.0	33.0
SN65LVDT33PWR	TSSOP	PW	16	2000	346.0	346.0	29.0
SN65LVDT34DR	SOIC	D	8	2500	346.0	346.0	29.0

## PW (R-PDSO-G\*\*)

#### 14 PINS SHOWN

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

## D (R-PDSO-G8)

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.



## D (R-PDSO-G16)

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AC.



# D(R-PDSO-G16)



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### **IMPORTANT NOTICE**

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

#### **Products Amplifiers** amplifier.ti.com Data Converters dataconverter.ti.com DSP dsp.ti.com Clocks and Timers www.ti.com/clocks Interface interface.ti.com Logic logic.ti.com Power Mgmt power.ti.com Microcontrollers microcontroller.ti.com www.ti-rfid.com RF/IF and ZigBee® Solutions www.ti.com/lprf

Applications	
Audio	www.ti.com/audio
Automotive	www.ti.com/automotive
Broadband	www.ti.com/broadband
Digital Control	www.ti.com/digitalcontrol
Medical	www.ti.com/medical
Military	www.ti.com/military
Optical Networking	www.ti.com/opticalnetwork
Security	www.ti.com/security
Telephony	www.ti.com/telephony
Video & Imaging	www.ti.com/video
Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2008, Texas Instruments Incorporated